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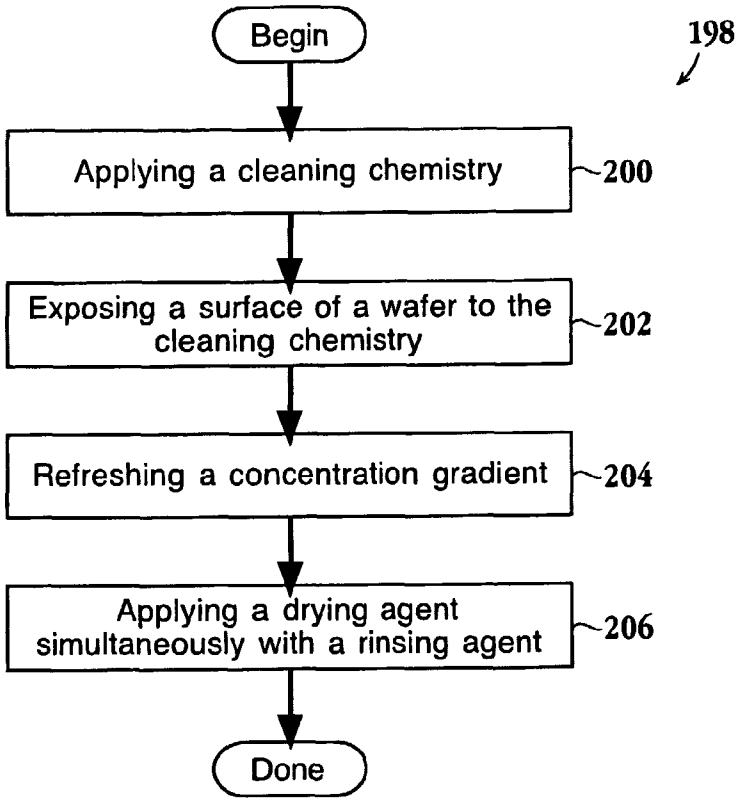
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(54) Title: APPARATUS AND METHOD FOR CONTROLLING GALVANIC CORROSION EFFECTS ON A SINGLE-WAFER CLEANING SYSTEM



(57) Abstract: A method and apparatus for controlling galvanic corrosion effects on a single-wafer cleaning system are provided. In one embodiment, a method for minimizing galvanic corrosion effects in a single-wafer cleaning system is provided. The method initiates with applying a cleaning chemistry containing corrosion inhibitors to a surface of a wafer. Then, the surface of the wafer is exposed to the cleaning chemistry for a period of time. Next, a concentration gradient at an interface of the cleaning chemistry and the surface of the wafer is refreshed. Then, a rinsing agent and a drying agent are applied simultaneously to remove the cleaning chemistry , wherein the drying agent dries the surface of the wafer prior to a concentration of the corrosion inhibitors being diluted to a level insufficient to provide corrosion protection.

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